

GOLD ON SILICON NITRIDE

Thick film gold on silicon nitride provides excellent wire bond adhesion, electrical conductivity and leach resistance.

Typical Properties of Gold Metallization System		
Resistivity		6.0 mΩ/sq
Printing Resolution	(line/space)	125 μm/125 μm
Wettability	(5 sec dip, 50 In/50 Pb solder)	95 – 100%
Adhesion*		
Initial		>68.9 MPa
Aged 250 h at -180°C		>68.9 MPa
Aged 500 h at 125°C		>68.9 MPa
Aged 1000 h at 125°C		>68.9 MPa
Wire Bond Strength		
Initial	(Au wire, 1.0 mil dia)	7.3 g
Aged 100 h at 125°C	(Au wire, 1.0 mil dia)	6.7 g
Aged 250 h at 125°C	(Au wire, 1.0 mil dia)	6.3 g

*Pull testing with 3.0 mm square pads and epoxy adhesive aluminum studs.

Sienna's technical team is ready to help you implement Silicon Nitride in your next generation of products.

Contact us for applications assistance and fast prototyping.

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